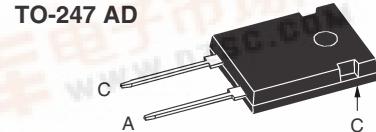
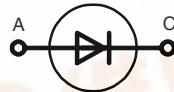


Fast Recovery Diode

SONIC-FRD™ series

I_{FAVM} = 60 A
V_{RRM} = 1400-1800 V
t_{rr} = 150 ns

V _{RSM}	V _{RRM}	Type
V	V	
1400	1400	DH 60-14A
1600	1600	DH 60-16A
1800	1800	DH 60-18A



A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings		
I _{FRMS}	T _{VJ} = T _{VJM}	100		A
I _{FAVM}	T _C = 89°C; rectangular, d = 0.5	60		A
I _{FRM}	t _p < 10 µs; rep. rating, pulse width limited by T _{VJM}	900		A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sine	650		A
E _{AS}	T _{VJ} = 25°C; non-repetitive I _{AS} = tbd A; L = 100 µH	tbd	mJ	
I _{AR}	V _A = 1.5·V _R typ.; f = 10 kHz; repetitive	tbd		A
T _{VJ}		-40...+150		°C
T _{VJM}		150		°C
T _{stg}		-40...+150		°C
P _{tot}	T _C = 25°C	415		W
M _d	Mounting torque	0.8...1.2		Nm
Weight		6		g

Symbol	Conditions	Characteristic Values		
		typ.	max.	
I _R	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	100	200	µA mA
V _F	I _F = 60 A; T _{VJ} = 125°C T _{VJ} = 25°C	2.7 2.3	2.7 2.7	V V
V _{TO}	For power-loss calculations only		1.95	V
r _T	T _{VJ} = T _{VJM}		12	mΩ
R _{thJC}		0.3		K/W
R _{thCH}		0.25		K/W
t _{rr}	I _F = 60 A; -di/dt = 600 A/µs; V _R = 1200 V;	150		ns
I _{RM}	T _{VJ} = 25°C	50		A
t _{rr}	I _F = 60 A; -di/dt = 600 A/µs; V _R = 1200 V;	350		ns
I _{RM}	T _{VJ} = 125°C	55		A

Data according to IEC 60747

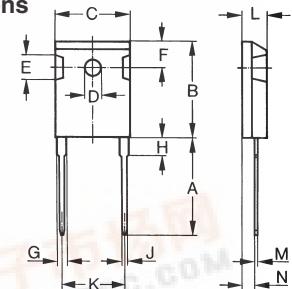
Features

- Small temperature dependence for
 - forward voltage drop
 - reverse recovery current
- Optimized for
 - dynamic avalanche ruggedness
 - low loss performance
- Exceptionally soft recovery
- Low reverse recovery current characteristic
- Soft recovery current without tail
- Optimized for high frequency hard switching

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Induction heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Dimensions



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D*	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

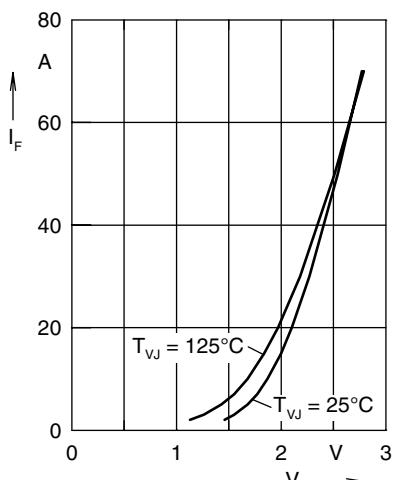


Fig. 1 Typ. forward current
 I_F versus V_F

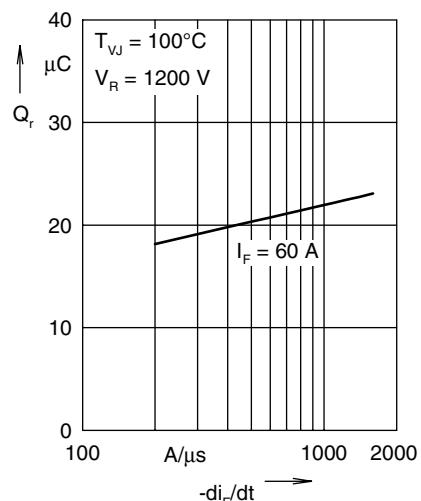


Fig. 2 Typ. reverse recovery charge
 Q_r versus $-di_F/dt$

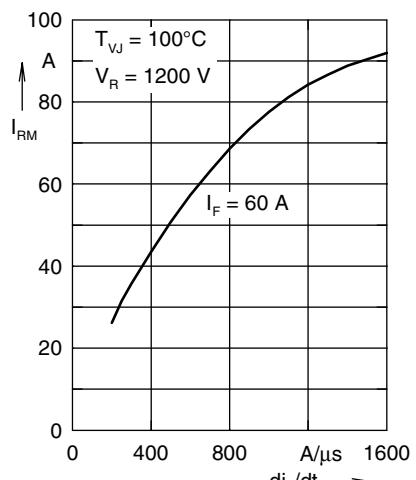


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

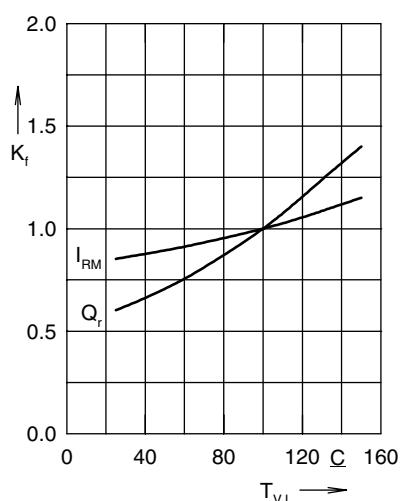


Fig. 4 Dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

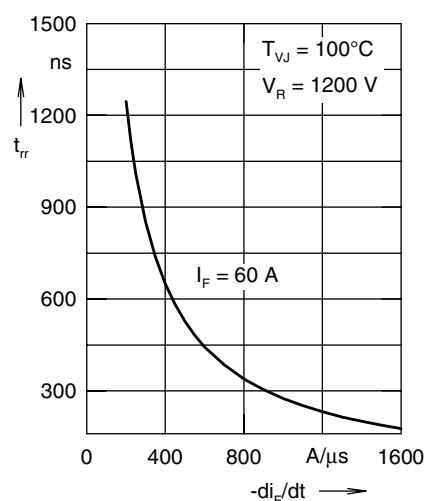


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

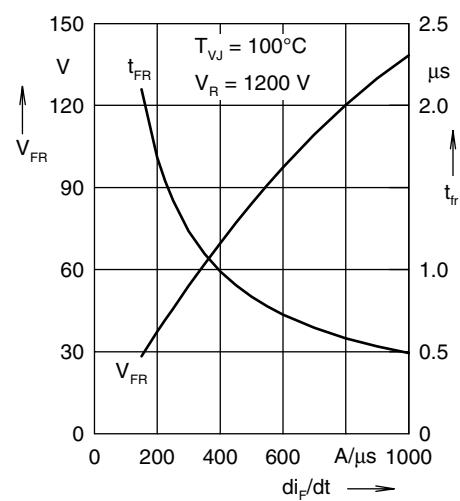


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{fr} versus di_F/dt

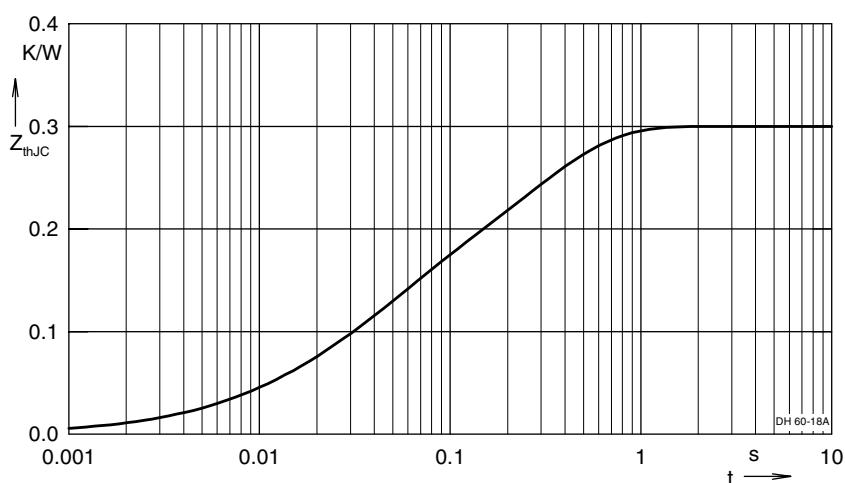


Fig. 7 Transient thermal resistance junction to case

NOTE: Fig. 2 to Fig. 6 shows typical values